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Ternary AlGe_xP alloy compounds for high capacity and rate capability of lithium ion battery anodes

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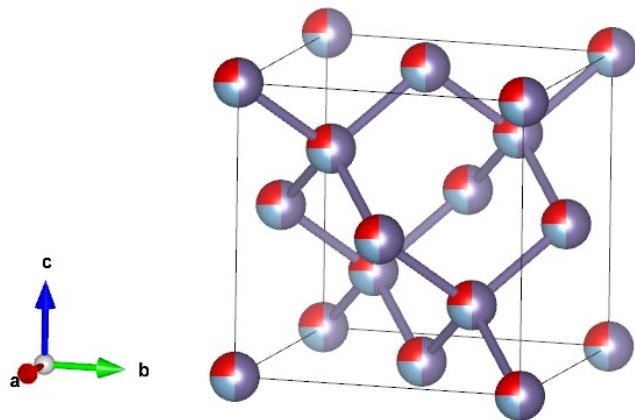


Fig. S1 Crystal structure of the as-synthesized AlGe_2P compound.

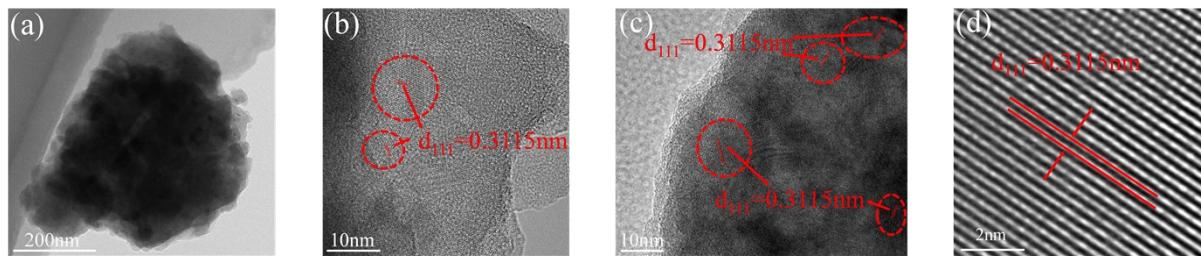


Fig. S2 (a) Low-magnitude TEM image; (b-d) HRTEM images of the as-synthesized AlGe_2P compound.

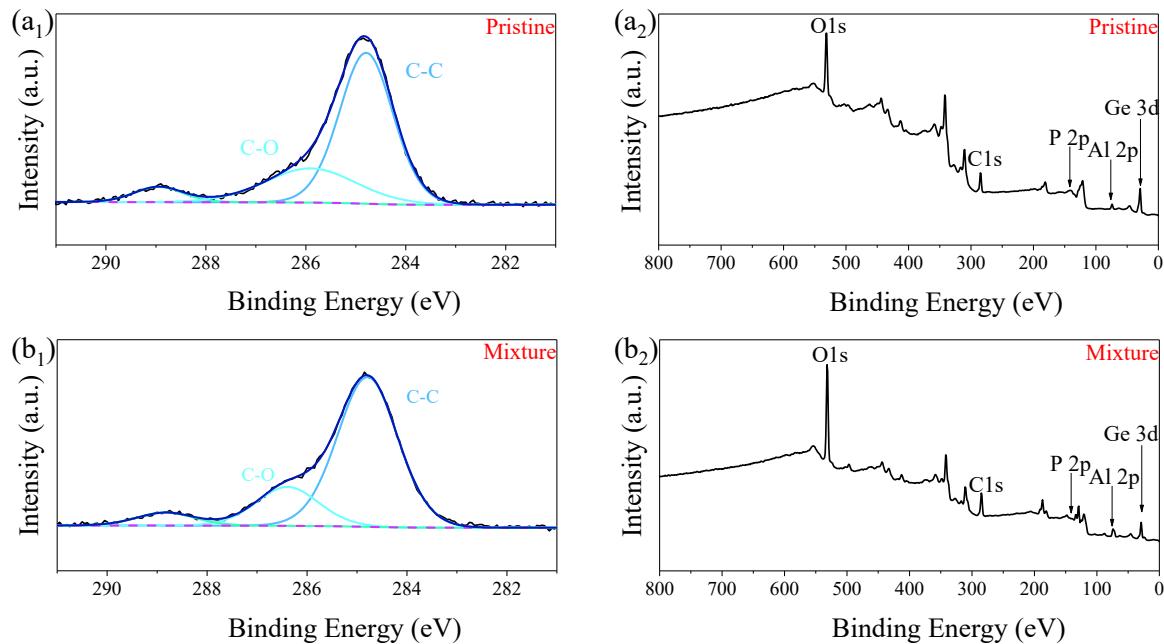


Fig. S3 High-resolution XPS spectra of C1s and full spectrum: (a) As-synthesized AlGe_2P powder; (b) The $\text{Al}+2\text{Ge}+\text{P}$ mixture.

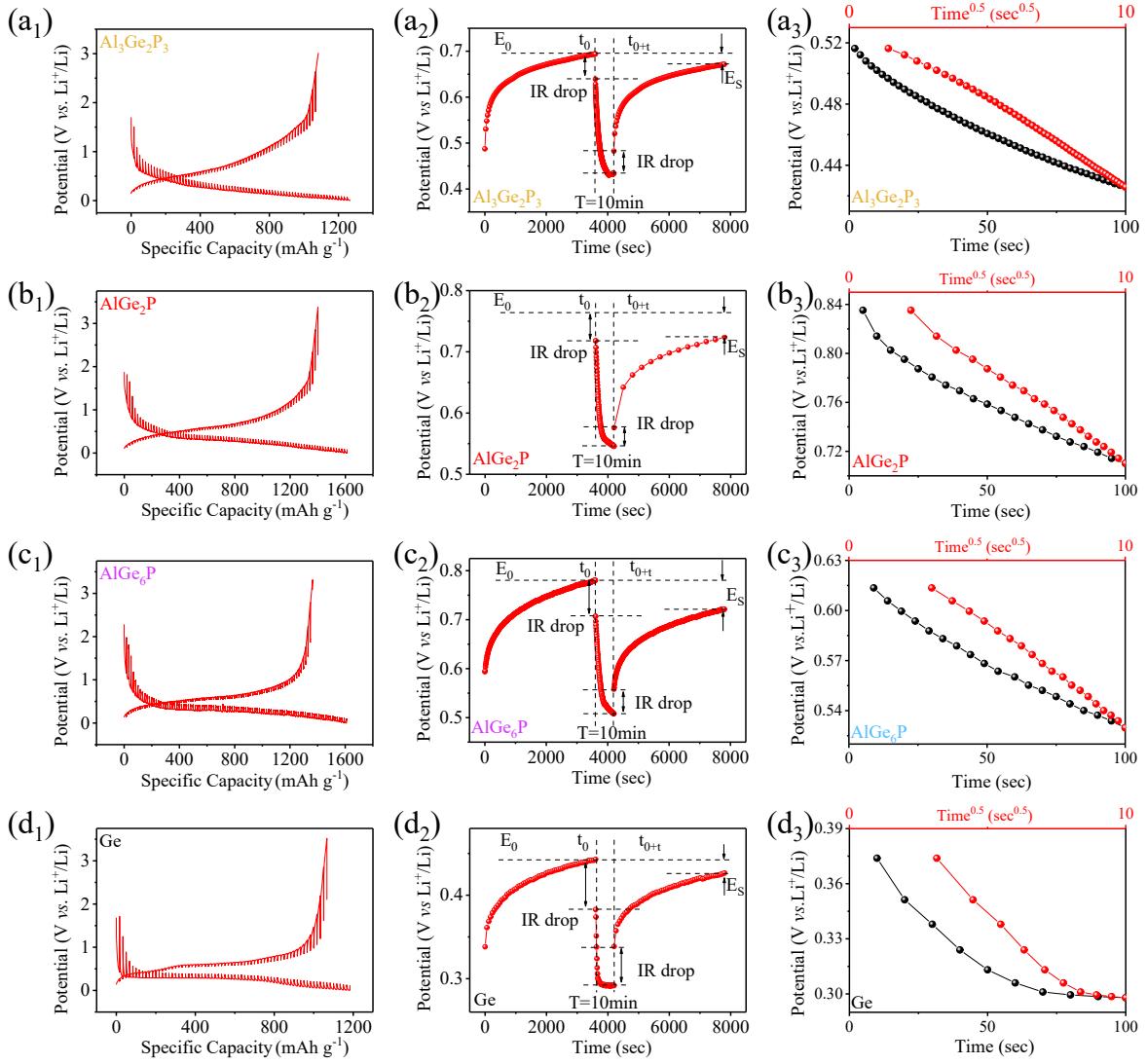


Fig. S4 GITT characterizations of the as-synthesized $\text{Al}_3\text{Ge}_2\text{P}_3$, AlGe_2P , AlGe_6P , and Ge samples: (a₁-d₁) First-cycle discharge and charge profiles; (a₂-d₂) Typical schemes of single-step GITT experiments; (a₃-d₃) $dE/dt^{(1/2)}$ curves. GITT measurement was carried out by imposing a 10 min pulse current rate at 0.1 A g^{-1} , and followed by 60 min relaxation interval for each pulse.

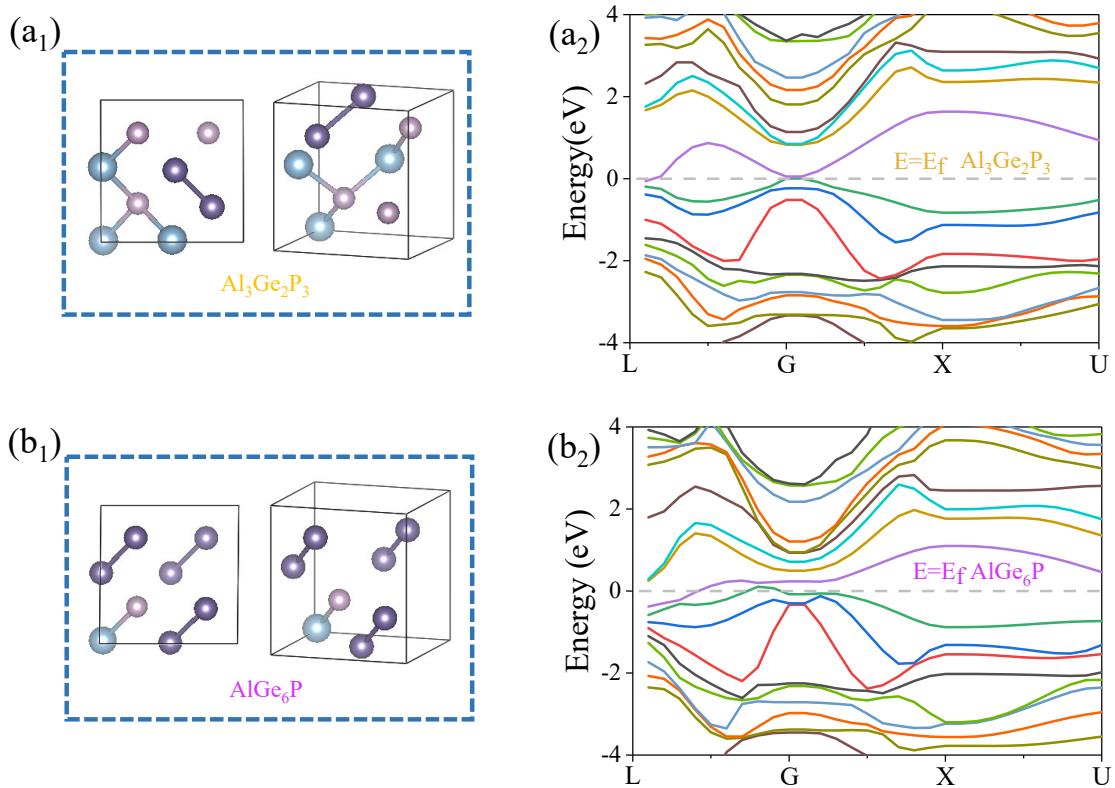


Fig. S5 (a₁-a₂): the structural model and electronic structure of the as-prepared $\text{Al}_3\text{Ge}_2\text{P}_3$ sample; (b₁-b₂) the structural model and electronic structure of the as-prepared AlGe_6P sample.

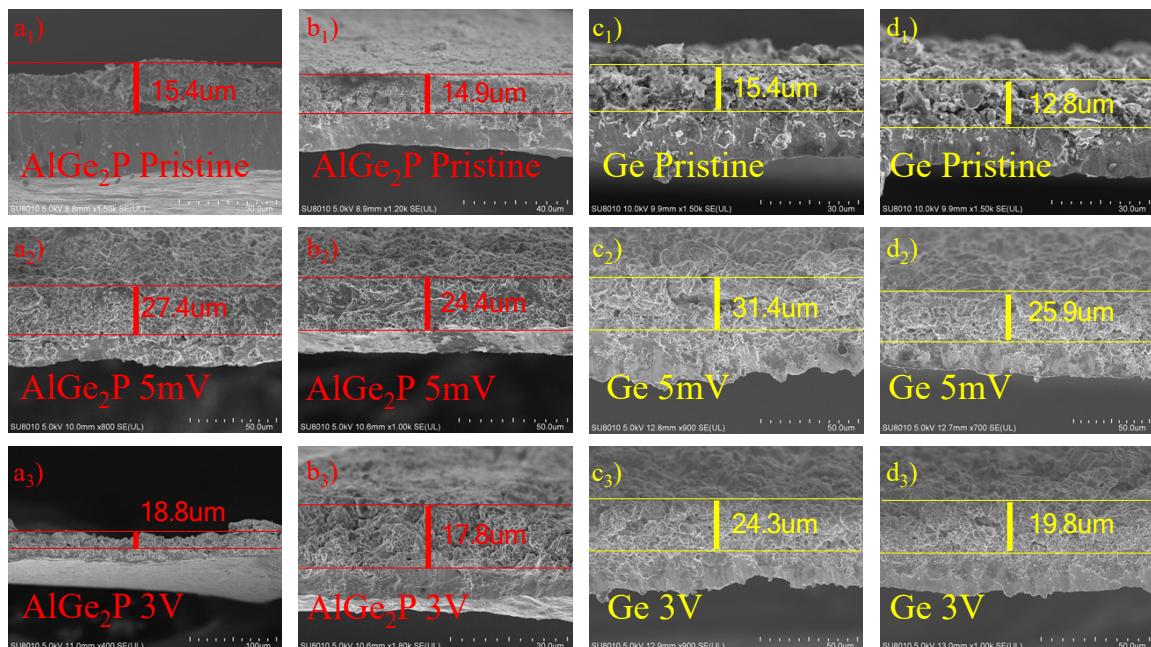


Fig. S6 Cross section images of AlGe_2P with Ge electrodes at the pristine state, discharging state of 0.005 V and charging state of 3.0 V. a, b) AlGe_2P electrodes; c, d) Ge electrodes.

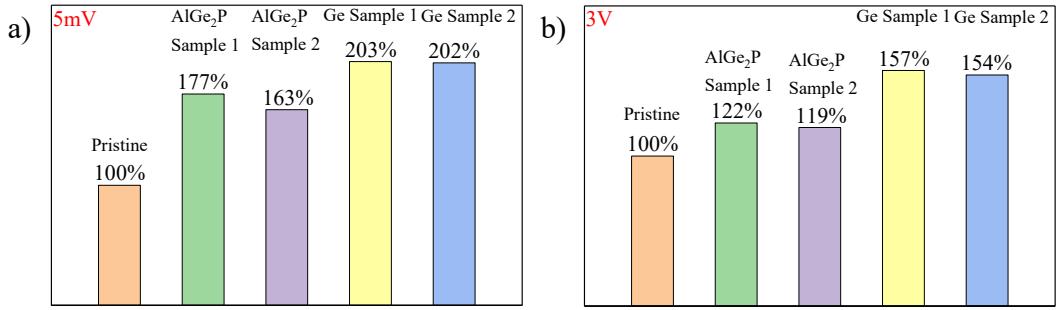


Fig. S7 Volume expansion rates of the AlGe₂P and Ge electrodes calculated based on Figure S6.

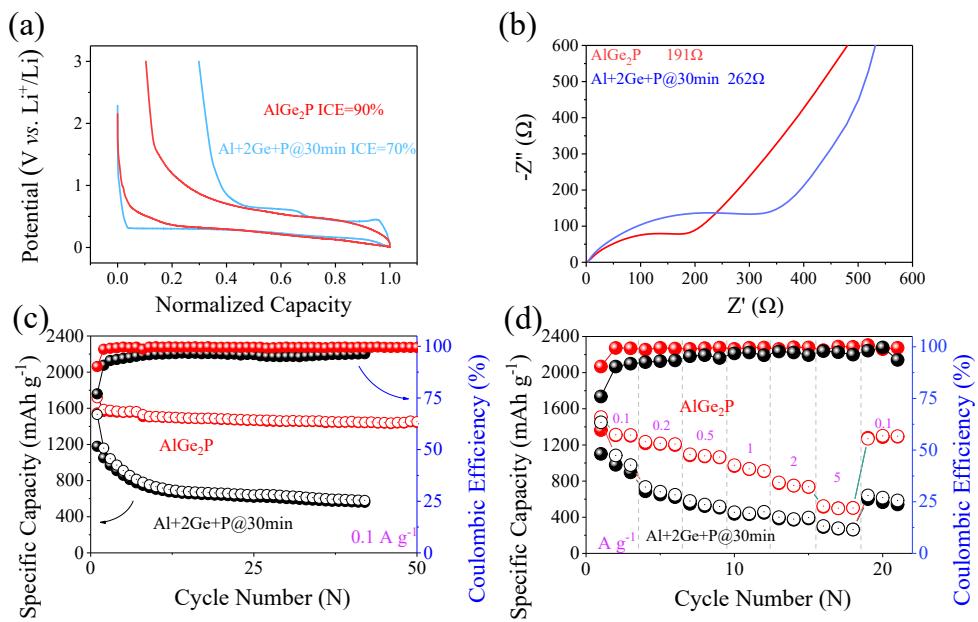


Fig. S8 Electrochemical characterizations of the AlGe₂P compound and the mixture of Al+2Ge+P: (a) First-cycle discharge and charge profiles; (b) Electrochemical impedance spectra; (c) Cycling stability; (d) Rate performance.

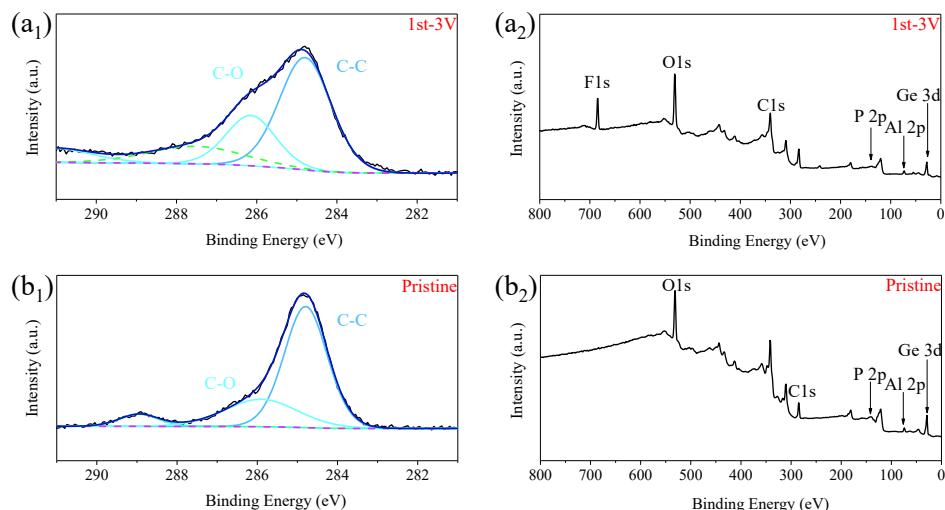


Fig. S9 XPS spectra of high-resolution C1s and full spectrum: (a) The as-prepared AlGe₂P compound; (b) The as-prepared AlGe₂P compound after cycling.

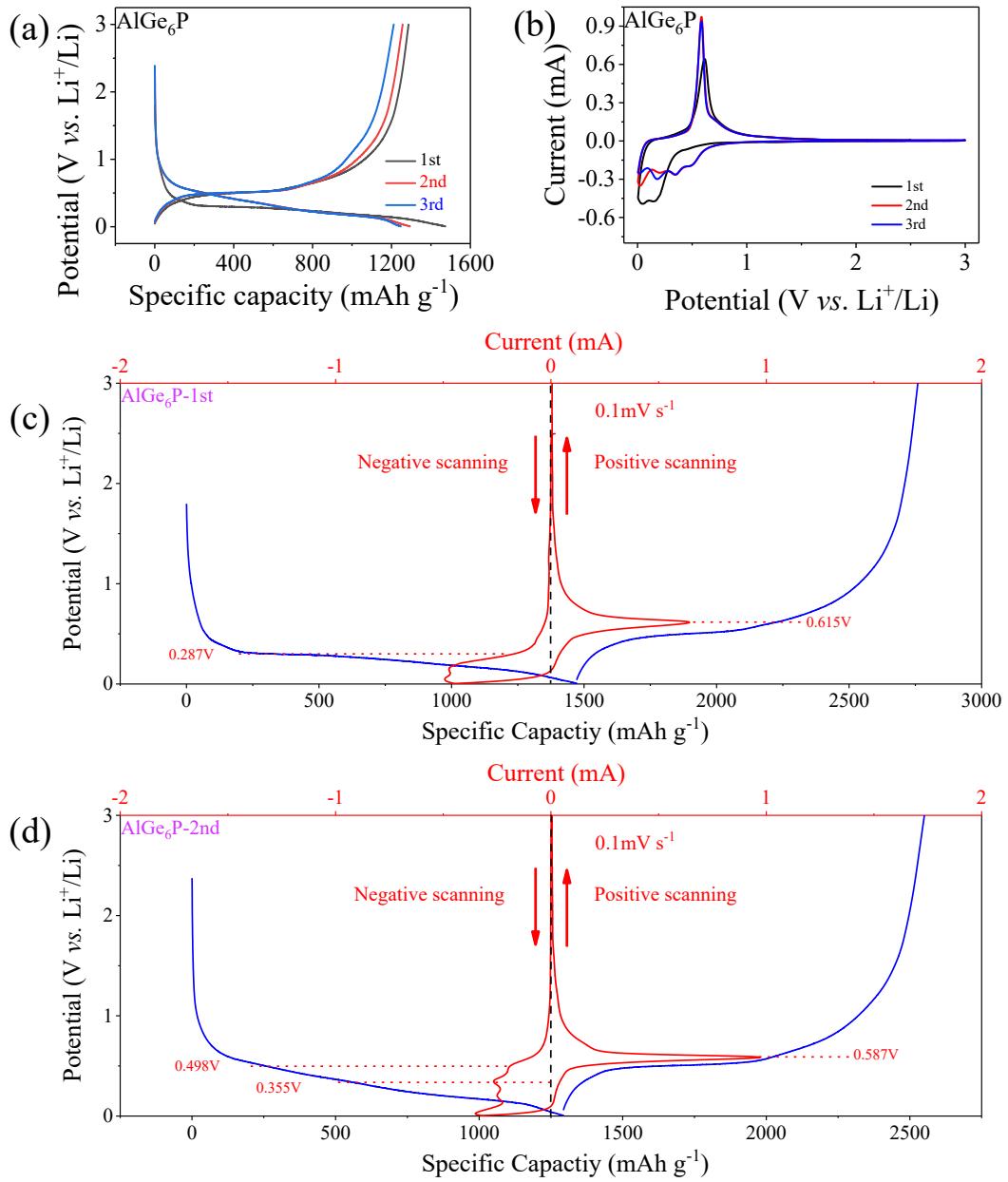


Fig. S10 Electrochemical characterizations of the as-synthesized AlGe_6P sample: (a) Initial three discharge and charge profiles at 100 mA g^{-1} ; (b) Cyclic voltammetry (CV) curves at 0.1 mV s^{-1} ; (c) First CV curves along with the first discharge and charge profiles; (d) Second CV curves along with the second discharge and charge profiles.

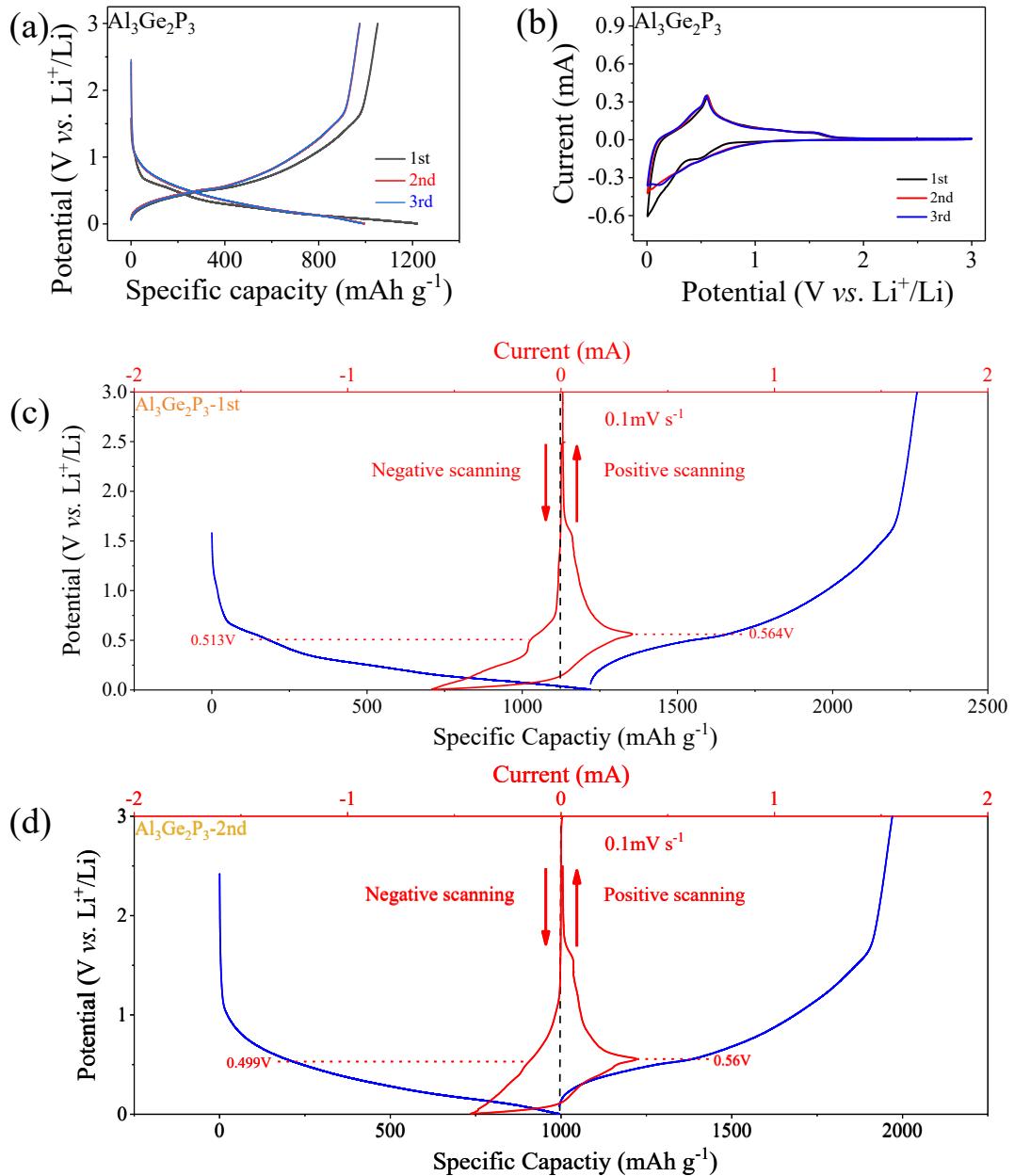


Fig. S11 Electrochemical characterizations of the as-synthesized $\text{Al}_3\text{Ge}_2\text{P}_3$ sample: (a) Initial three discharge and charge profiles at 100 mA g^{-1} ; (b) Cyclic voltammetry (CV) curves at 0.1 mV s^{-1} ; (c) First CV curves along with the first discharge and charge profiles; (d) Second CV curves along with the second discharge and charge profiles.

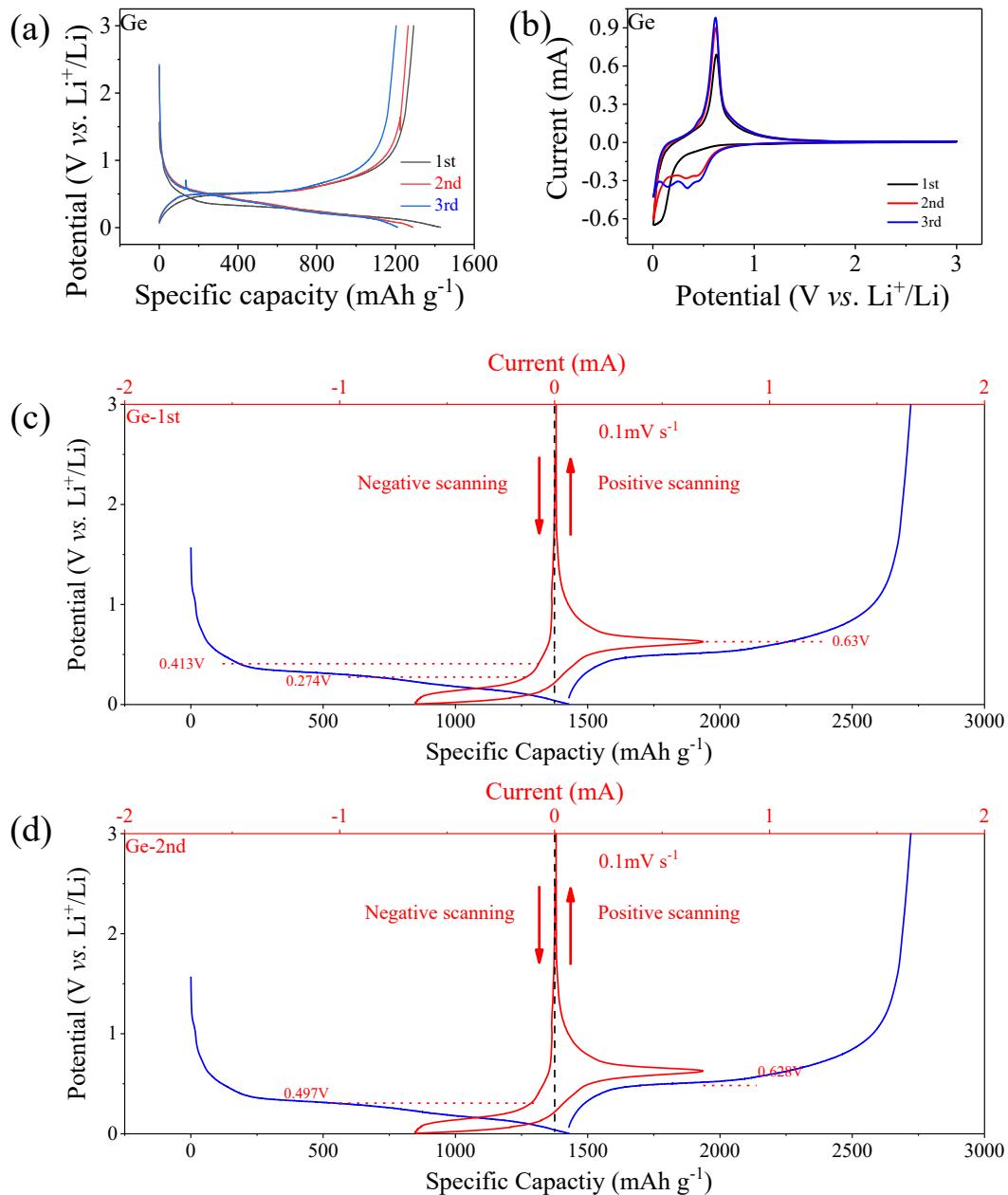


Fig. S12 Electrochemical characterizations of the single-component phase of Ge sample: (a) Initial three discharge and charge profiles at 100 mA g^{-1} ; (b) Initial three cyclic voltammetry (CV) curves at 0.1 mV s^{-1} ; (c) First CV curves along with the first discharge and charge profiles; (d) Second CV curves along with the second discharge and charge profiles.

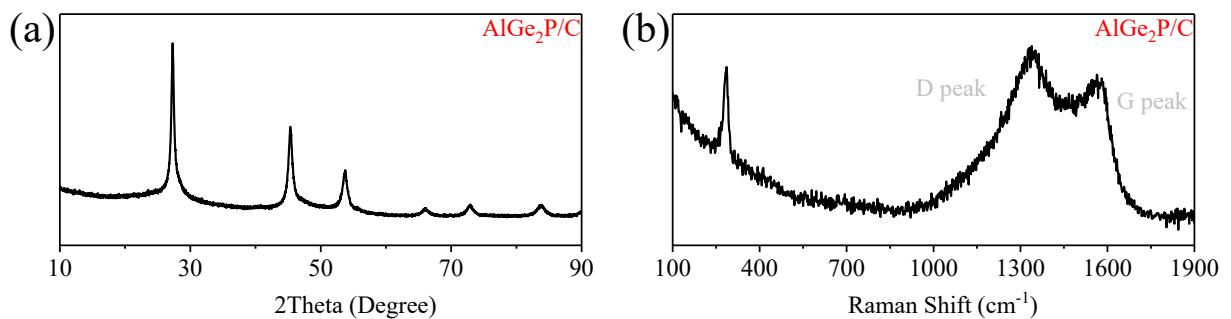


Fig. S13 (a) XRD pattern; (b) Raman spectrum of the as-synthesized AlGe₂P/C.

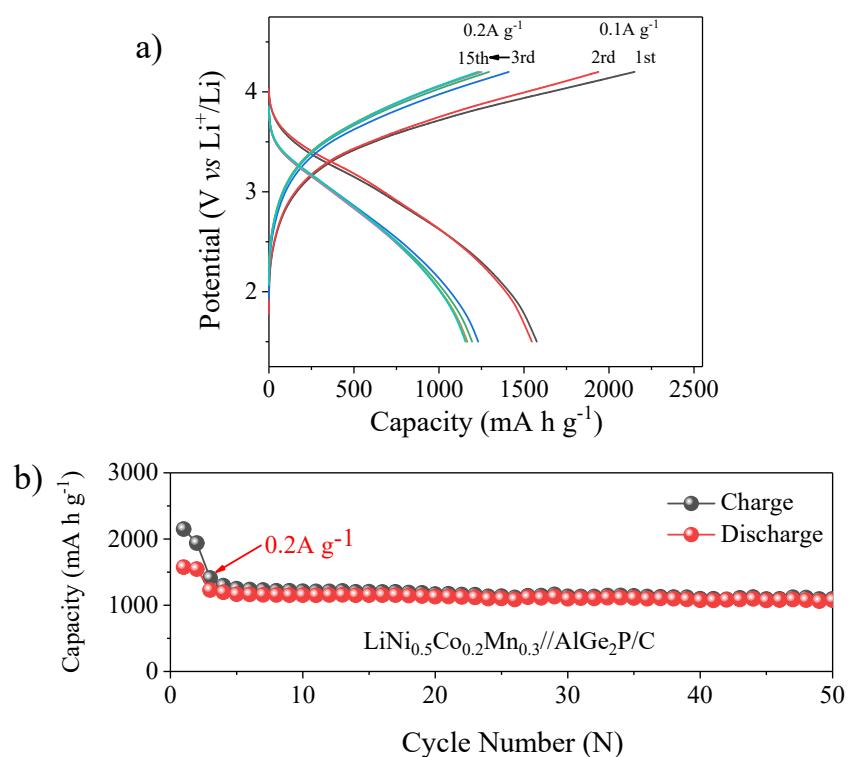


Fig. S14 a) Discharge and charge profiles, and b) Cycling stability of the LiNi_{0.5}Co_{0.2}Mn_{0.3}O₂//AlGe₂P/C full cell.

Table S1. Main parameters of processing and refinement of the as-prepared AlGe₂P compound.

Compound	AlGe ₂ P
Crystal System	Cubic
Space Group	Fd-3m
A, Å	5.767342
V, Å ³	191.1
2θ-interval, °	10–90
Z	1

Table S2. Fractional atomic coordinates and isotropic displacement parameters of the as-synthesized AlGe₂P compound.

	X	Y	Z	Occ
Al	0	0	0	1/4
Ge	0	0	0	1/2
P	0	0	0	1/4

Table S3. Comparison of cyclic and rate performances.

Materials	Cycle performance	Rate performance	Reference
AlGe ₂ P	2A g ⁻¹ , 800cycles, 867 mA h g ⁻¹	20A g ⁻¹ , 454 mA h g ⁻¹	This work
GeO ₂ /Ge	1A g ⁻¹ , 40cycles, 520.2 mA h g ⁻¹	5A g ⁻¹ , 124.6 mA h g ⁻¹	[39]
Ge/3DPG-2	0.5C, 250cycles, 931 mA h g ⁻¹	5C, 494mA h g ⁻¹	[40]
np-GeSn ₅	0.2A g ⁻¹ , 500cycles, 520.2 mA h g ⁻¹	1.5A g ⁻¹ , 778 mA h g ⁻¹	[41]
GeCH ₃ /rGO-2	1A g ⁻¹ , 500cycles, 288 mA h g ⁻¹	5A g ⁻¹ , 227 mA h g ⁻¹	[42]
mGe-500	0.5C, 100cycles, 785 mA h g ⁻¹	1C, 655mA h g ⁻¹	[43]
Ge/3DOM-Ni	0.2C, 100cycles, 610 mA h g ⁻¹	10C, 270mA h g ⁻¹	[44]
GeH	1C, 100cycles, 341 mA h g ⁻¹	2C, 265mA h g ⁻¹	[45]
Ge/C	0.1C, 50cycles, 1095 mA h g ⁻¹	2C, 972mA h g ⁻¹	[46]
CuGeO ₃ @RGO	2A g ⁻¹ , 300cycles, 550 mA h g ⁻¹	1A g ⁻¹ , 879 mA h g ⁻¹	[47]
PC-Ge NW	0.16A g ⁻¹ , 50cycles, 789 mA h g ⁻¹	1.6A g ⁻¹ , 540 mA h g ⁻¹	[48]